

Schottky Diodes

Features

- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

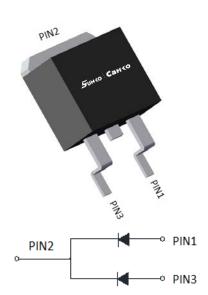
Mechanical Data

• Package: TO-263

Molding compound meets UL 94 V-0 flammability rating -

• Terminals: Tin plated leads, solderable per J-STD-

002 and JESD22-B102
• Polarity: As marked



■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBRBL1060CT
Device marking code			MBRBL1060CT
Repetitive Peak Reverse Voltage	VRRM	V	60
Average Rectified Output Current @60Hz sine wave, R-load, T _C =138°C	IO	Α	10
Surge(Non-repetitive)Forward Current @60H _Z half sine-wave, 1 cycle, T _a =25°C	IFSM	Α	100
Current Squared Time @1ms≤t≤8.3ms Tj=25°C	l²t	A ² s	41
Storage Temperature	T _{stg}	°	-55 ~ +150
Junction Temperature	Tj	Ç	-55 ~ + 150

■Electrical Characteristics (T_a=25°C Unless otherwise specified)

==iooti ioti olialaotoliotioo xxa == = = = ========================				
PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBRBL1060CT
Maximum instantaneous forward voltage drop per diode	VFM	٧	IFM=5.0A	0.6
Maximum DC reverse current at rated DC blocking voltage per diode	IRRM1	mA	VRM=VRRM T _a =25°C	0.2
	IRRM2		VRM=VRRM T _a =100°C	20

Note1:Pulse test:300uS pulse widh,1% duty cycle

Note2:Pulse test:pulse widh 40mS



Thermal Characteristics $(T_a=25^{\circ}\mathbb{C} \text{ Unless otherwise specified})$

PARA	METER	SYMBOL	UNIT	MBRBL1060CT
Thermal Resistance	Between junction and case	R ₀ J-C	°CW	2.0

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MPDDI 40000T	Approximate 1.43	50	2000	8000	Tube
MBRBL1060CT	Approximate 1.43	1000	2000	10000	Reel

■Characteristics (Typical)

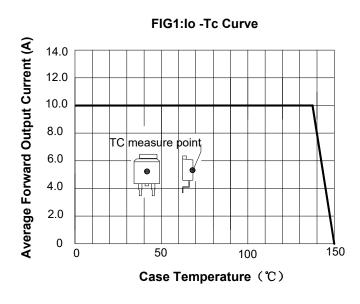
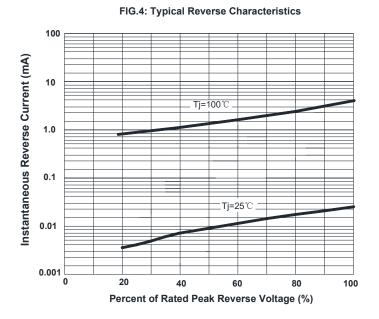


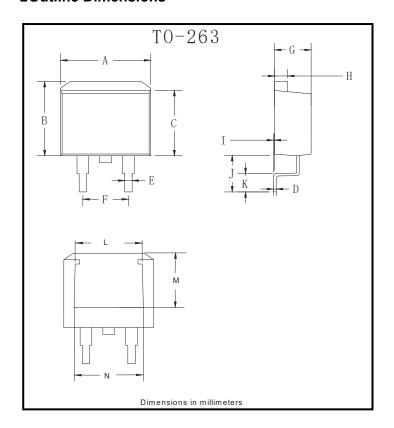
FIG2:Surge Forward Current Capability 140 Peak Forward Surge Current (A) 120 100 8.3ms Single Half Sine-Wave 80 JEDEC Method 60 20 2 5 20 50 10 100 **Number of Cycles**

FIG3: Forward Voltage 50 Instantaneous Forward Current (A) 20 10 5.0 1.0 0.5 0.2 Ta=25℃ 0.1 0 0.2 0.5 0.6 0.7 0.8 0.9 1.0 Instantaneous Forward Voltage (V)



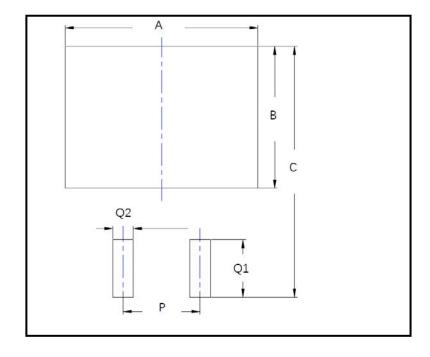


■Outline Dimensions



TO-263				
Dim	Min	Max		
Α	9.5	11.5		
В	9.7	10.5		
С	8.4	9.0		
D	0.28	0.64		
Е	0.68	0.94		
F	4.55	5.6		
G	4.04	5.10		
Н	1.14	1.4		
I	0	0.2		
J	4.9	6.05		
K	1.79	2.79		
L	7.3	7.9		
М	6.2	6.8		
N	7.6	8.2		

■Suggested Pad Layout



Dim	Millimeters	
Α	12.7	
В	9.4	
С	16.6	
Р	5.08	
Q1	3.8	
Q2	1.35	



Disclaimer

The information presented in this document is for reference only. Shanghai Sunco Electronics Co., Ltd reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Russiansunco or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website http:// www.russiansunco.com, or consult your nearest Russiansunco's sales office for further assistance.